

Abstract of the Disclosure

5 A planar slice (1) of semiconductor substrate material of a first conductivity type is provided on one face with a first region (13a) of a second conductivity type having a higher dopant concentration than that of the substrate and on the opposite face a second region (13b) of said second conductivity type having a higher dopant concentration than that of the substrate. Each of the faces has had removed from part of it a depth of  
10 material which increases gradually as the outer edge is approached so that the junction between each of the regions (13a, 13b) and the substrate is exposed along a path following the shape of the perimeter of the slice but so that the removal of material ceases at a distance outwardly beyond the exposure of the junction to leave a rim (11) of the original planar faces of the slice at its perimeter.

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